Mubashir A Kharadi

List of Publications by Year
in descending order

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19	215	1162889	1058333
papers	citations	8	14
		h-index	g-index

19	19	19	155
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Dilute magnetic semiconductor electrode based all semiconductor magnetic tunnel junction for high-temperature applications. Physica B: Condensed Matter, 2022, 627, 413525.	1.3	5
2	Electric field tunable spin polarization in functionalized silicene. Physics Letters, Section A: General, Atomic and Solid State Physics, 2022, 429, 127952.	0.9	2
3	Temperature-Dependent High Magnetoresistance in Zigzag Silicene Nanoribbon Heterostructure. IEEE Transactions on Electron Devices, 2022, 69, 4010-4015.	1.6	1
4	Silicene/MoS₂ Heterojunction for High-Performance Photodetector. IEEE Transactions on Electron Devices, 2021, 68, 138-143.	1.6	20
5	Silicene-Based Spin Filter With High Spin-Polarization. IEEE Transactions on Electron Devices, 2021, 68, 5095-5100.	1.6	2
6	Comparative study of optical properties of substitutionally doped La2NiMnO6 double perovskite ceramic: A potential candidate for solar cells and dielectrics. Physica B: Condensed Matter, 2021, 621, 413311.	1.3	16
7	First principle study of fluorine functionalized germanene based two probe device. Physica B: Condensed Matter, 2021, 620, 413249.	1.3	1
8	Performance analysis of functionalized silicene nanoribbon â€based photodetector. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2021, 34, .	1.2	6
9	Spin field effect transistors and their applications: A survey. Microelectronics Journal, 2020, 106, 104924.	1.1	15
10	Modelling for triple gate spinâ€FET and design of triple gate spinâ€FETâ€based binary adder. IET Circuits, Devices and Systems, 2020, 14, 464-470.	0.9	6
11	Hydrogenated silicene based magnetic junction with improved tunneling magnetoresistance and spin-filtering efficiency. Physics Letters, Section A: General, Atomic and Solid State Physics, 2020, 384, 126826.	0.9	13
12	Simulation of Triple Gate Spin Field-Effect Transistor and its Applications to Digital Logic. , 2020, , .		1
13	Electronic Properties of Fluorine Functionalized Germanene Nanoribbons. , 2020, , .		2
14	Performance analysis of indium phosphide channel based sub-10 nm double gate spin field effect transistor. Physics Letters, Section A: General, Atomic and Solid State Physics, 2020, 384, 126498.	0.9	8
15	Reviewâ€"Silicene: From Material to Device Applications. ECS Journal of Solid State Science and Technology, 2020, 9, 115031.	0.9	65
16	Negative differential resistance in gate all-around spin field effect transistors. Nanosystems: Physics, Chemistry, Mathematics, 2020, 11, 301-306.	0.2	4
17	Electrically reconfigurable logic design using multi-gate spin Field Effect Transistors. Microelectronics Journal, 2019, 90, 278-284.	1.1	11
18	Sub-10-nm Silicene Nanoribbon Field Effect Transistor. IEEE Transactions on Electron Devices, 2019, 66, 4976-4981.	1.6	37

#	Article	IF	Citations
19	Photo-Detectors Based on Two Dimensional Materials. , 0, , .		0